

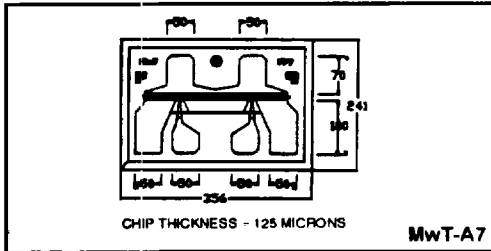


MwT - A7

18 GHz High Gain, Low Noise
GaAs FET

MicroWave Technology

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FEATURES

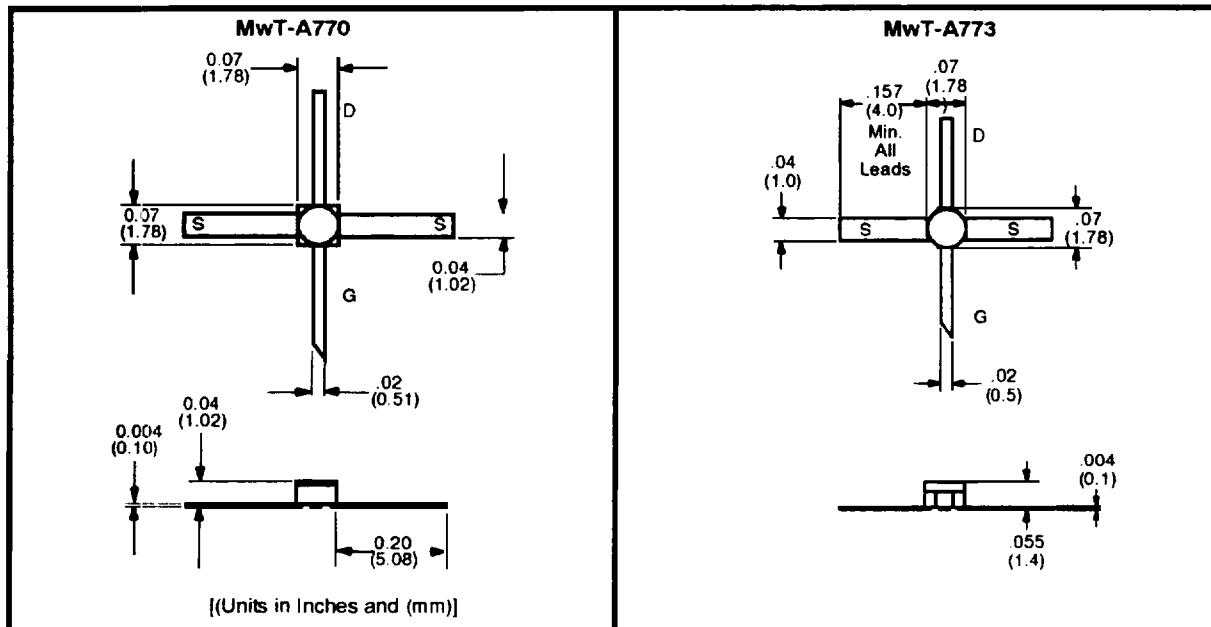
- HIGH AVAILABLE GAIN WHEN BIASED FOR LOW-NOISE
- EXCELLENT FOR BROADBAND GAIN OR OSCILLATOR BUFFER APPLICATIONS
- 0.3 MICRON REFRACTORY METAL / GOLD GATE
- 250 MICRON GATE WIDTH
- CHOICE OF CHIP AND TWO PACKAGE TYPES

DESCRIPTION

The MwT-A7 is a GaAs MESFET device whose nominal quarter-micron gate length and 250 micron gate width make it ideally suited to applications requiring high-gain in the 500 MHz to 18 GHz frequency range while exhibiting low noise figure. The straight gate geometry of the MwT-A7 makes it equally effective for either wideband (ex. 6 to 18 GHz) or narrow-band applications. Processing which guarantees low phase noise makes the MwT-A7 particularly attractive for oscillator applications. The chip is produced using MwT's reliable metal system and all devices are screened to insure reliability. All chips are passivated using MwT's patented "Diamond-Like Carbon" process for durability with no degradation in performance. Designers can use MwT's unique BIN selection feature to choose devices from narrow Idss ranges, insuring consistent circuit operation.

RF SPECIFICATIONS AT Ta = 25°C

SYMBOL	PARAMETERS AND CONDITIONS	FREQ	UNITS	MwT-A7GN MwT-A770GN MwT-A773GN			MwT-A7SN MwT-A770SN MwT-A773SN			MwT-A7LN MwT-A770LN MwT-A773LN		
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX
NFopt	Optimum Noise Figure VDS = 3.0 V IDS = 10 mA	12 GHz	dB		2.0	2.2		1.7	2.0		1.5	1.8
GA	Gain at Optimum Noise Figure VDS = 3.0 V IDS = 10 mA	12 GHz	dB	7.0	8.0		7.0	8.0		7.0	8.0	
P1dB	Output Power at 1dB Compression VDS=5.0V IDS= 0.6 IDSS	12 GHz	dBm		16.0			17.0			17.0	
SSG	Small Signal Gain VDS=5.0V IDS=0.6 IDSS	12 GHz	dB	9.0	10.0		9.5	11.0		9.5	11.0	



KHMVSO11X

DC SPECIFICATIONS AT Ta = 25 °C

SYMBOL	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
Idss	Saturated Drain Current Vds = 3.0 V VGS = 0.0 V	mA	26		98
Gm	Transconductance Vds = 3.0 V VGS = 0.0 V	mS	36	45	
Vp	Pinch-off Voltage Vds = 3.0 V IDS = 1.0 mA	V		-1.5	-4.5
BVGSO	Gate-to-Source Breakdown Voltage Igs = -0.4 mA, Igd = 0	V	-5.0	-8.0	
BVGDO	Gate-to-Drain Breakdown Voltage Igd = -0.4 mA, Igs = 0	V	-6.0	-8.0	
Rth	Thermal Resistance MwT-A7 Chip MwT-A770, A773	°C/W			180 380*

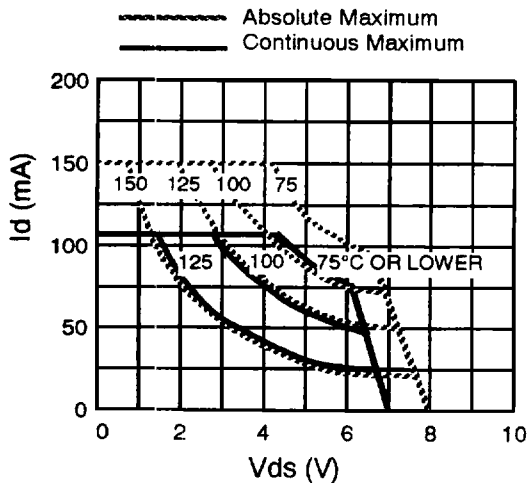
* Overall Rth depends on case mounting

MAXIMUM RATINGS AT Ta = 25 °C

SYMBOL	PARAMETER	UNITS	CONT MAX ¹	ABSOLUTE MAX ²
VDS	Drain to Source Voltage	V	See Safe Operating Limits	
Tch	Channel Temperature	°C	+150	+175
Tst	Storage Temperature	°C	-65 to +150	+175
Pin	RF Input Power	mW	125	250

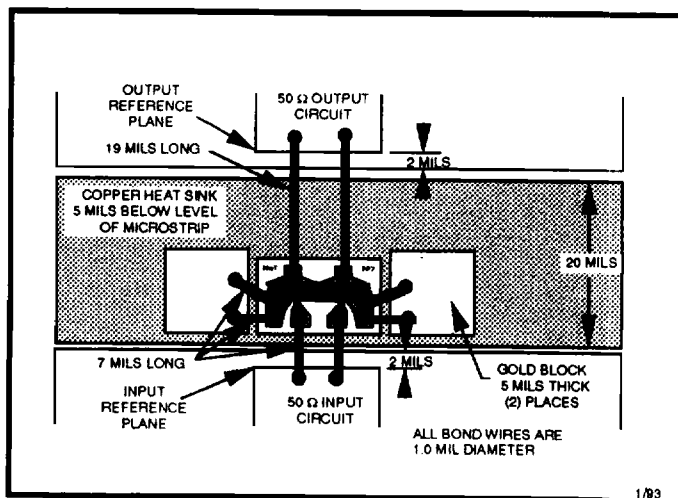
- NOTES: 1. Exceeding any one of these limits in continuous operation may reduce the mean-time-to-failure below the design goals.
 2. Exceeding any one of these limits may cause permanent damage.

SAFE OPERATING LIMITS vs. Case Temperature



RECOMMENDED ASSEMBLY CONFIGURATION

Shown below is the assembly and bonding configuration used for S-Parameter measurements of the MwT-A7 Chip and is recommended for optimum performance. For self-bias applications the gold blocks may be replaced by capacitors. Contact MwT for additional applications information.

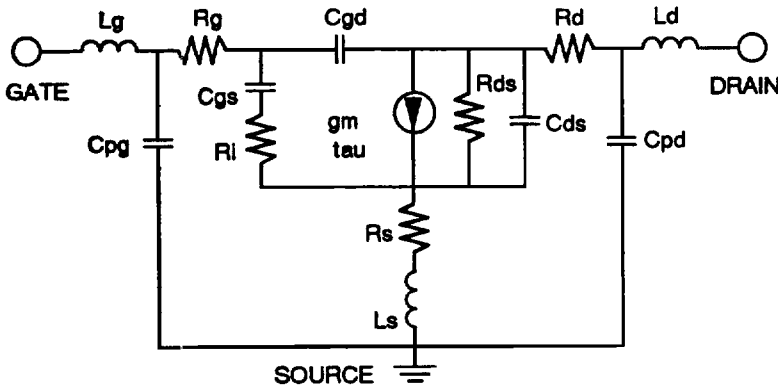




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DEVICE EQUIVALENT CIRCUIT MODEL



PARAMETER		VALUE
Gate Bond Wire Inductance	Lg	.084 nH
Gate Pad Capacitance	Cpg	.134 pF
Gate Resistance	Rg	0.19 Ω
Gate-Source Capacitance	Cgs	.227 pF
Channel Resistance	Ri	6.1 Ω
Gate-Drain Capacitance	Cgd	.017 pF
Transconductance	gm	57 mS
Transit time	tau	1.53 psec
Source Resistance	Rs	3.75 Ω
Source Inductance	Ls	.061 nH
Drain-Source Resistance	Rds	184 Ω
Drain-Source Capacitance	Cds	.020 pF
Drain Resistance	Rd	3.89 Ω
Drain Pad Capacitance	Cpd	.076 pF
Drain Inductance	Ld	.175 nH

BIN SELECTION

Every MwT-A7 wafer produced is 100% DC probed, binned by Idss in 4 ma increments, and sample devices are evaluated for RF performance. Users may select devices from 18 Idss bins to insure consistent matched performance in the circuit. The shaded bins are typically available in smaller quantity and caution is advised before designing these bins into high production applications. Availability in three visual grades insures the most economical solution for the application.

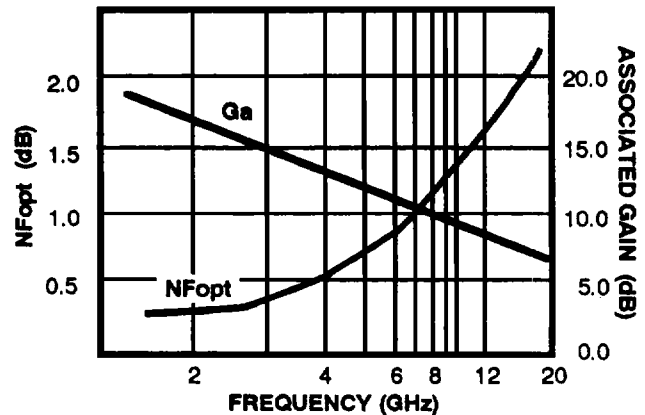
BIN #	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
IDSS (mA)	26-30	30-34	34-38	38-42	42-46	46-50	50-54	54-58	58-62	62-66	66-70	70-74	74-78	78-82	82-86	86-90	90-94	94-98

TYPICAL NOISE PARAMETERS

MwT-A7LN Chip: VDS = 3.0 V, IDS = 12 mA

FREQUENCY MHz	NF MIN dB	GAMMA OPT		Rn/50
		MAG	ANGLE	
1000	0.30	0.95	3.7	0.55
2000	0.33	0.86	19.1	0.48
4000	0.60	0.73	38.5	0.41
6000	0.86	0.62	58.3	0.37
10000	1.33	0.51	98.6	0.33
12000	1.55	0.49	117.7	0.31
16000	1.96	0.51	150.4	0.29
18000	2.15	0.53	163.7	0.27

NOISE FIGURE AND ASSOCIATED GAIN VS. FREQUENCY



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TYPICAL COMMON SOURCE SCATTERING PARAMETERS

MwT-A7 CHIP BIASED FOR LOW NOISE FIGURE: VDS = 3.0 V, IDS = 10 mA

FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	.98	-11.5	2.26	168.5	.02	78.0	.66	-5.7
2.00	.95	-21.3	2.20	160.2	.04	73.0	.65	-11.9
3.00	.95	-31.6	2.18	151.1	.06	67.3	.64	-17.8
4.00	.93	-42.2	2.12	141.7	.08	61.3	.63	-23.5
5.00	.91	-52.1	2.05	133.2	.09	55.6	.61	-29.2
6.00	.89	-61.2	1.99	125.4	.11	50.2	.59	-34.3
7.00	.88	-70.4	1.93	117.3	.12	44.7	.58	-39.4
8.00	.86	-79.5	1.85	109.1	.13	39.2	.56	-44.6
9.00	.84	-87.5	1.77	102.1	.14	33.6	.54	-49.8
10.00	.84	-96.2	1.71	95.1	.14	27.4	.51	-55.1
12.00	.80	-110.8	1.57	81.4	.14	17.6	.48	-64.6
14.00	.78	-121.7	1.45	69.5	.15	13.9	.45	-73.8
16.00	.78	-130.9	1.34	58.8	.15	6.2	.44	-85.4
18.00	.80	-139.4	1.28	48.2	.15	-1.0	.43	-95.4
20.00	.79	-148.5	1.18	37.4	.14	-9.6	.41	-107.3
22.00	.76	-152.9	1.09	28.6	.14	-10.5	.46	-117.5
24.00	.76	-155.7	1.05	19.7	.14	-17.8	.47	-126.4
26.00	.76	-160.1	1.02	10.2	.14	-30.2	.47	-135.4

MwT-A7 CHIP BIASED FOR GAIN & POWER: VDS = 5.0 V, IDS = .5 IDSS = 29 mA

FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	.98	-14.3	3.66	167.1	.02	76.5	.70	-5.4
2.00	.95	-26.7	3.53	157.7	.03	71.3	.69	-11.3
3.00	.94	-39.5	3.46	147.4	.04	65.2	.68	-16.7
4.00	.91	-52.1	3.29	137.4	.06	59.1	.66	-21.8
5.00	.88	-63.7	3.13	128.3	.06	53.5	.64	-26.6
6.00	.86	-74.0	2.98	120.2	.07	49.2	.62	-30.8
7.00	.84	-84.3	2.83	112.0	.08	44.2	.61	-34.9
8.00	.82	-93.9	2.66	104.0	.08	39.3	.59	-39.2
9.00	.81	-102.2	2.51	97.2	.09	34.7	.57	-43.4
10.00	.80	-111.4	2.40	90.4	.09	28.9	.55	-47.6
12.00	.77	-125.6	2.15	77.4	.08	21.9	.52	-54.9
14.00	.76	-135.5	1.94	66.6	.08	24.0	.51	-62.9
16.00	.77	-143.9	1.79	56.2	.09	18.4	.49	-73.3
18.00	.79	-151.8	1.68	46.0	.08	15.2	.49	-81.8
20.00	.78	-160.3	1.53	35.8	.07	9.4	.47	-91.7
22.00	.76	-164.1	1.43	27.2	.08	16.3	.53	-102.4
24.00	.76	-166.7	1.37	18.4	.08	11.4	.55	-111.4
26.00	.75	-171.6	1.32	8.9	.08	-1.5	.53	-121.3



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TYPICAL COMMON SOURCE SCATTERING PARAMETERS

MwT-A770 BIASED FOR LOW NOISE FIGURE: VDS = 3.0 V, IDS = 10 mA

FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	.97	-23.1	2.06	158.1	.02	68.9	.67	-18.6
2.00	.93	-42.8	1.88	139.1	.04	55.9	.66	-33.6
3.00	.88	-58.8	1.70	123.1	.06	46.2	.66	-45.2
4.00	.82	-73.5	1.58	108.8	.07	34.3	.63	-54.9
5.00	.76	-86.4	1.51	97.2	.06	25.2	.60	-61.0
6.00	.75	-102.2	1.53	83.5	.06	28.9	.59	-70.5
8.00	.71	-141.3	1.61	54.3	.11	-5.3	.48	-97.7
10.00	.74	171.4	1.65	15.6	.08	-37.2	.42	-138.1
12.00	.85	132.3	1.46	-20.3	.06	-40.2	.49	170.2
14.00	.93	110.3	1.18	-51.2	.06	-52.6	.66	139.5
16.00	.81	92.4	1.00	-81.2	.05	-65.8	.74	126.3
18.00	.70	63.2	.81	-110.2	.04	-52.8	.68	107.0
20.00	.65	33.4	.94	-146.2	.07	-125.0	.67	83.4

MwT-A770 BIASED FOR GAIN & POWER: VDS = 5.0 V, IDS = 0.5 IDSS = 29 mA

FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	.96	-26.6	3.63	156.0	.02	69.0	.71	-17.5
2.00	.91	-49.1	3.24	135.5	.03	55.0	.70	-32.0
3.00	.84	-66.5	2.85	118.6	.04	47.9	.68	-42.9
4.00	.77	-82.3	2.58	103.7	.04	36.5	.65	-52.2
5.00	.70	-95.8	2.43	91.8	.04	31.6	.62	-57.4
6.00	.68	-111.5	2.40	77.9	.03	55.2	.62	-66.1
8.00	.63	-154.2	2.42	48.5	.06	10.4	.53	-91.0
10.00	.67	159.1	2.41	10.7	.04	3.8	.52	-124.5
12.00	.80	120.2	2.15	-24.6	.06	22.2	.55	-172.8
14.00	.86	98.2	1.71	-57.9	.07	-2.0	.71	150.5
16.00	.72	79.8	1.42	-89.0	.08	-22.1	.81	131.9
18.00	.59	53.3	1.09	-118.6	.08	-25.5	.77	110.1
20.00	.51	24.3	1.19	-153.7	.07	-76.9	.78	88.0





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TYPICAL COMMON SOURCE SCATTERING PARAMETERS

MwT-A773 BIASED FOR LOW NOISE FIGURE: VDS = 3.0 V, IDS = 10 mA

FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	.97	-20.2	1.74	161.2	.03	72.2	.65	-14.8
2.00	.94	-37.8	1.63	144.4	.05	59.8	.64	-27.4
3.00	.91	-52.3	1.53	129.3	.07	50.4	.63	-38.0
4.00	.85	-65.7	1.45	115.4	.08	39.8	.60	-46.7
5.00	.79	-76.6	1.39	104.8	.09	31.8	.58	-51.9
6.00	.76	-91.3	1.44	92.5	.10	28.8	.56	-60.1
8.00	.70	-129.6	1.55	67.2	.15	2.5	.42	-86.1
10.00	.70	-179.0	1.61	31.4	.14	-29.3	.32	-131.8
12.00	.81	139.1	1.41	-0.9	.11	-41.9	.38	-176.0
14.00	.90	118.0	1.20	-28.8	.10	-55.4	.49	159.7
16.00	.82	94.4	1.03	-62.3	.09	-68.3	.54	134.7
18.00	.70	65.1	.79	-88.1	.07	-59.5	.55	115.7
20.00	.73	36.2	.77	-115.1	.09	-85.9	.64	98.0

MwT-A773 BIASED FOR GAIN & POWER: VDS = 5.0 V, IDS = 0.5 IDSS = 29 mA

FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	.96	-24.4	3.79	158.7	.02	70.8	.71	-14.6
2.00	.91	-45.4	3.46	139.9	.04	57.2	.69	-27.2
3.00	.85	-62.1	3.12	123.7	.05	49.7	.67	-36.6
4.00	.77	-77.7	2.87	109.0	.06	39.6	.64	-44.4
5.00	.68	-90.2	2.68	98.1	.05	32.9	.61	-47.6
6.00	.65	-106.9	2.70	85.6	.05	38.1	.60	-53.8
8.00	.60	-153.1	2.73	59.9	.08	11.5	.46	-73.3
10.00	.63	157.8	2.66	25.0	.06	-8.9	.38	-108.7
12.00	.78	121.3	2.27	-5.0	.06	4.8	.41	-155.1
14.00	.85	103.4	1.90	-33.2	.08	-8.2	.52	177.1
16.00	.75	78.6	1.63	-67.0	.09	-20.4	.59	149.0
18.00	.61	48.4	1.22	-94.9	.10	-20.3	.60	127.9
20.00	.64	20.4	1.17	-121.5	.12	-46.2	.71	109.5

